

## BSS138W

### 50V N-Channel MOSFET

220mA 50V;  $R_{DS(ON)typ}=1.0\Omega@10V$ ,  $R_{DS(ON)typ}=1.1\Omega@4.5V$

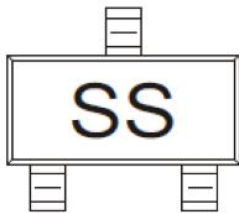
#### FEATURE

- High density cell design for extremely low  $R_{DS(on)}$
- Rugged and Reliable

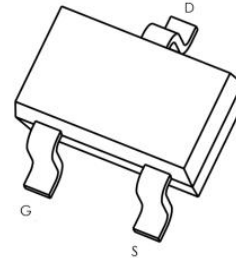
#### Application

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

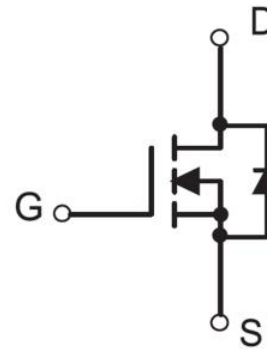
#### MARKING:



SOT-323



Schematic diagram



#### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	0.22	A
Power Dissipation	$P_D$	300	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ\text{C}$

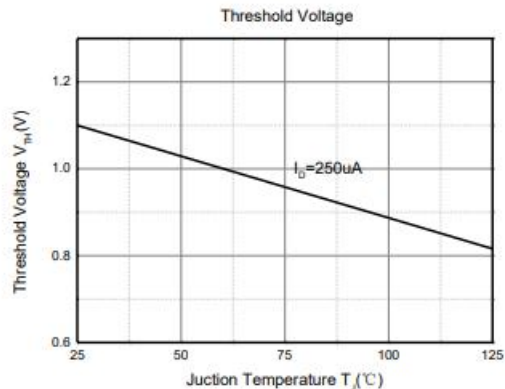
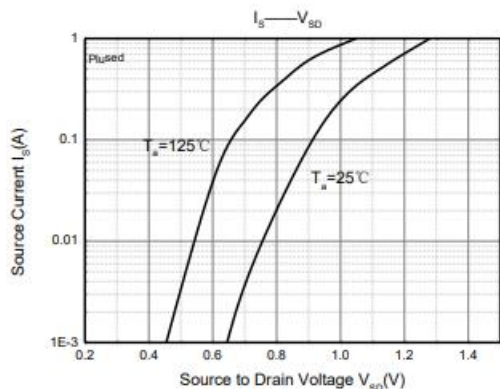
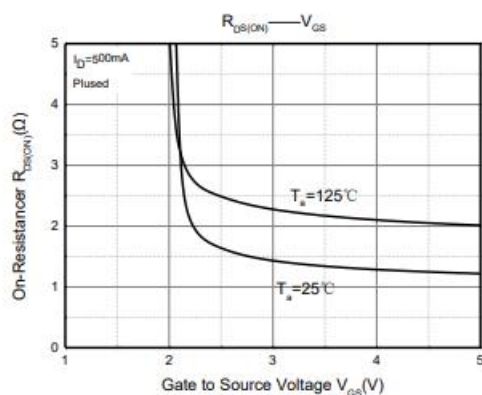
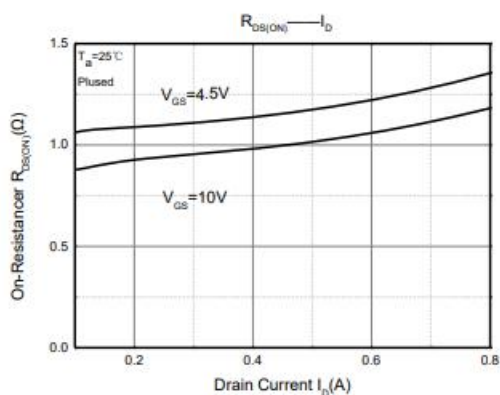
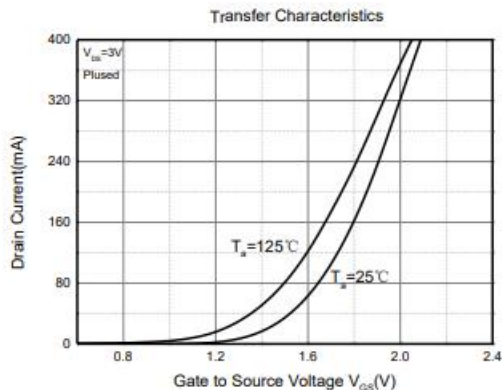
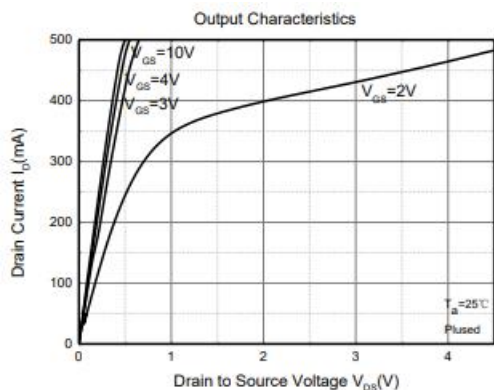
**MOSFET ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>STATIC CHARACTERISTICS</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	50			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V			0.1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage <sup>(1)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.8		1.5	V
Drain-source on-resistance <sup>(1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 220mA		1.2	3.5	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 30mA		1.1	5.0	
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 220mA		1.2	6.0	
3.Forward tranconductance <sup>(1)</sup>	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 220mA		0.13		S
<b>DYNAMIC CHARACTERISTICS<sup>(2)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		26.5		pF
Output Capacitance	C <sub>oss</sub>			12.9		
Reverse Transfer Capacitance	C <sub>rss</sub>			5.9		
<b>SWITCHING CHARACTERISTICS<sup>(1,2)</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 30V, I <sub>D</sub> = 290mA, R <sub>G</sub> = 6Ω			5	ns
Turn-on rise time	t <sub>r</sub>				18	
Turn-off delay time	t <sub>d(off)</sub>				36	
Turn-off fall time	t <sub>f</sub>				14	
<b>SOURCE-DRAIN DIODE CHARACTERISTICS<sup>(1)</sup></b>						
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 440mA, V <sub>GS</sub> = 0V			1.4	V

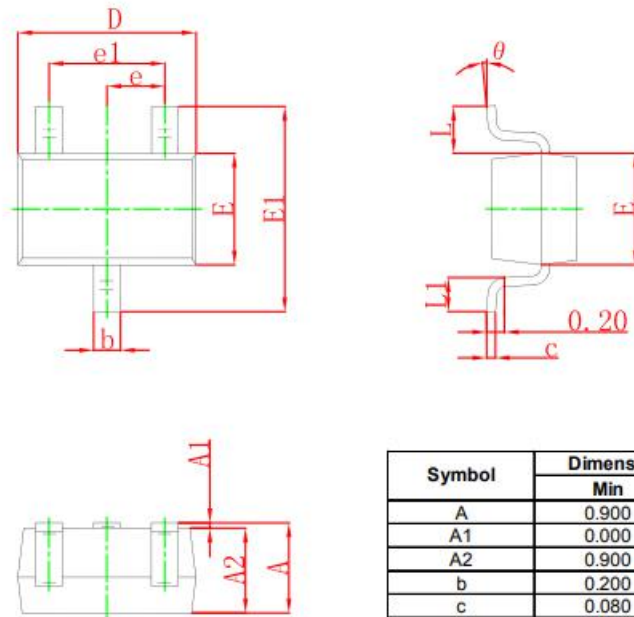
**Notes:**

1. Pulse Test ; Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. These parameters have no way to verify.

**Typical Electrical and Thermal Characteristics**



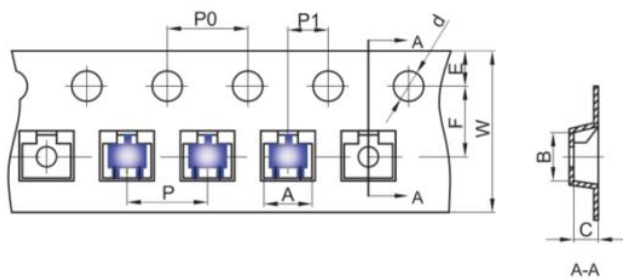
## SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

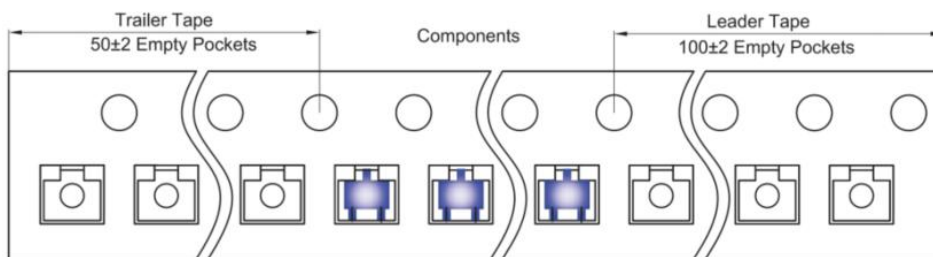
SOT-323 Tape and Reel

SOT-323 Embossed Carrier Tape

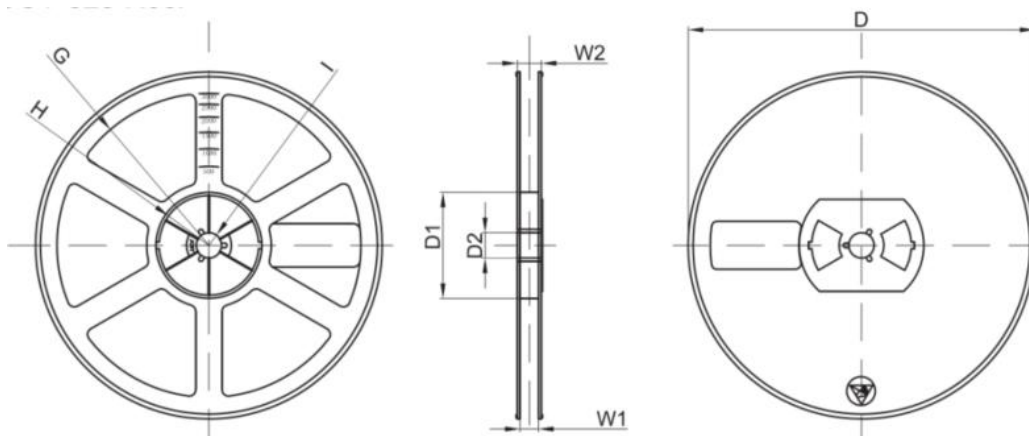


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-323	2.25	2.55	1.19	Ø1.55	1.75	3.50	4.00	4.00	2.00	8.00

SOT-323 Tape Leader and Trailer



SOT-323 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	